
2SA1190, 2SA1191

Silicon PNP Epitaxial

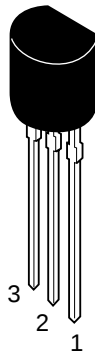
HITACHI

Application

- Low frequency low noise amplifier
- Complementary pair with 2SC2855 and 2SC2856

Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

2SA1190, 2SA1191

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	2SA1190	2SA1191	Unit
Collector to base voltage	V _{CBO}	−90	−120	V
Collector to emitter voltage	V _{CEO}	−90	−120	V
Emitter to base voltage	V _{EBO}	−5	−5	V
Collector current	I _C	−100	−100	mA
Emitter current	I _E	100	100	mA
Collector power dissipation	P _C	400	400	mW
Junction temperature	T _j	150	150	°C
Storage temperature	T _{stg}	−55 to +150	−55 to +150	°C

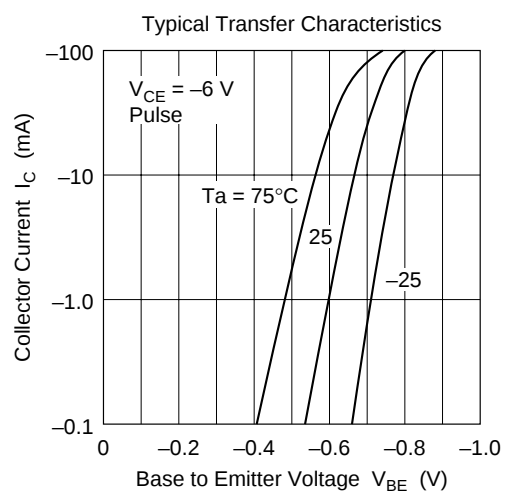
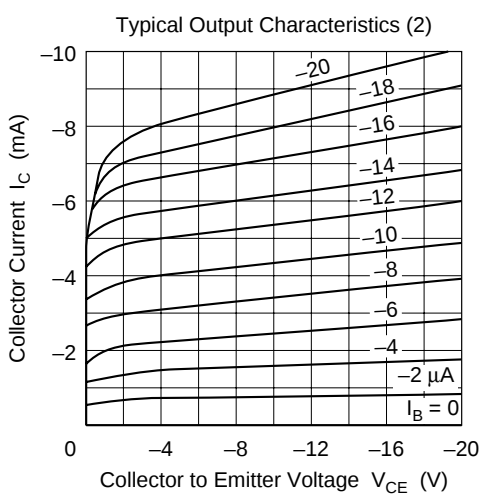
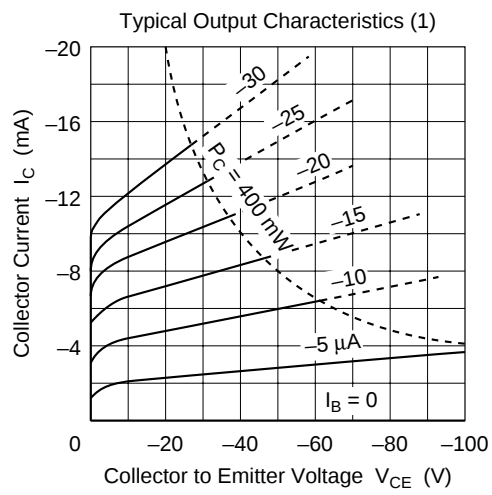
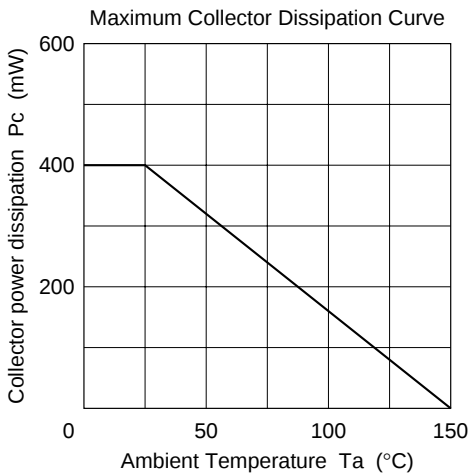
Electrical Characteristics (Ta = 25°C)

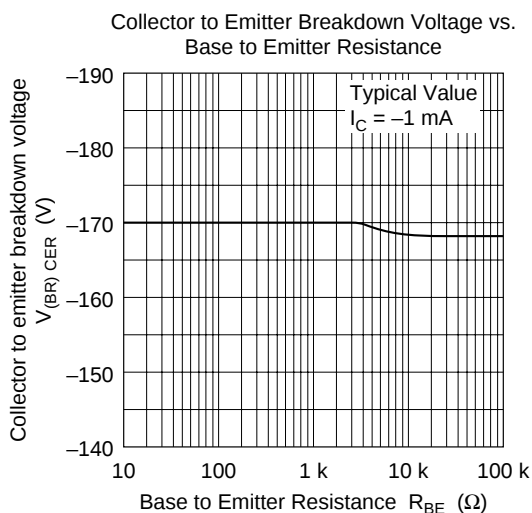
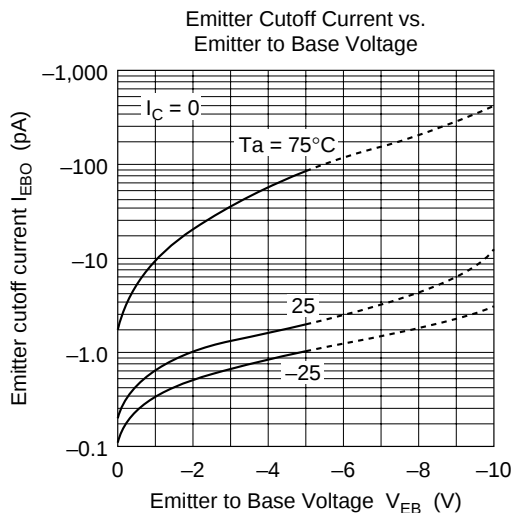
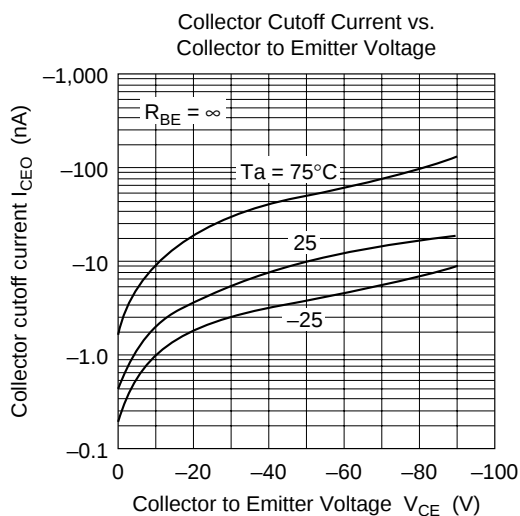
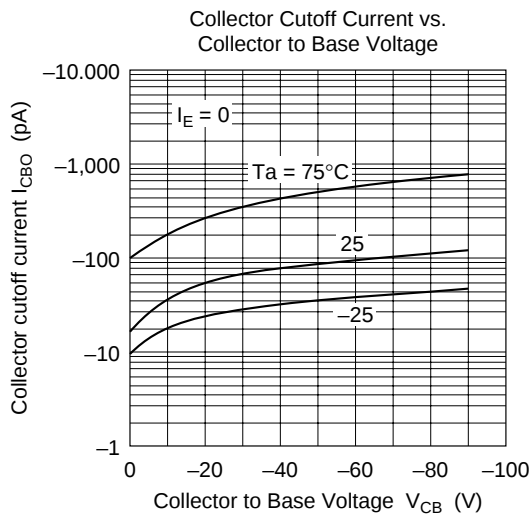
Item	Symbol	2SA1190			2SA1191			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	-90	—	—	-120	—	—	V	$I_C = -10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-90	—	—	-120	—	—	V	$I_C = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	-5	—	—	V	$I_E = -10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-0.1	—	—	-0.1	μA	$V_{CB} = -70 \text{ V}, I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	-0.1	—	—	-0.1	μA	$V_{EB} = -2 \text{ V}, I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	250	—	800	250	—	800		$V_{CE} = -12 \text{ V},$ $I_C = -2 \text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	-0.05	-0.15	—	-0.05	-0.15	V	$I_C = -10 \text{ mA},$ $I_B = -1 \text{ mA}^{*2}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	-0.7	-1.0	—	-0.7	-1.0	V	
Gain bandwidth product	f_T	—	130	—	—	130	—	MHz	$V_{CE} = -6 \text{ V},$ $I_C = -10 \text{ mA}$
Collector output capacitance	Cob	—	3.2	—	—	3.2	—	pF	$V_{CB} = -10 \text{ V}, I_E = 0,$ $f = 1 \text{ MHz}$
Noise figure	NF	—	0.15	1.5	—	0.15	1.5	dB	$V_{CE} = -6 \text{ V},$ $I_C = -0.1 \text{ mA},$ $R_g = 10 \text{ k}\Omega$ $f = 1 \text{ kHz}$
		—	0.2	2.0	—	0.2	2.0	dB	$V_{CE} = -6 \text{ V},$ $I_C = -0.1 \text{ mA},$ $R_g = 10 \text{ k}\Omega$ $f = 10 \text{ Hz}$
Noise voltage referred to input	e_n	—	0.7	—	—	0.7	—	nV/ $\sqrt{\text{Hz}}$	$V_{CB} = -6 \text{ V},$ $I_C = -10 \text{ mA},$ $R_g = 0, f = 1 \text{ kHz}$

Notes: 1. The 2SA1190 and 2SA1191 are grouped by h_{FE} as follows.

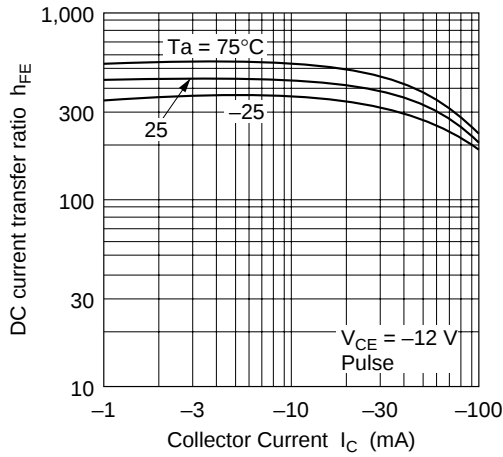
2. Pulse test

D	E
250 to 500	400 to 800

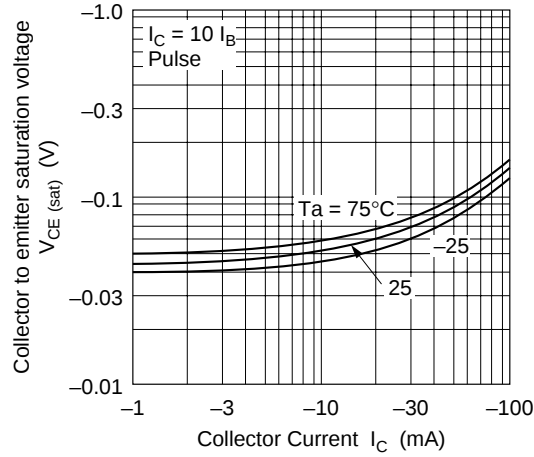




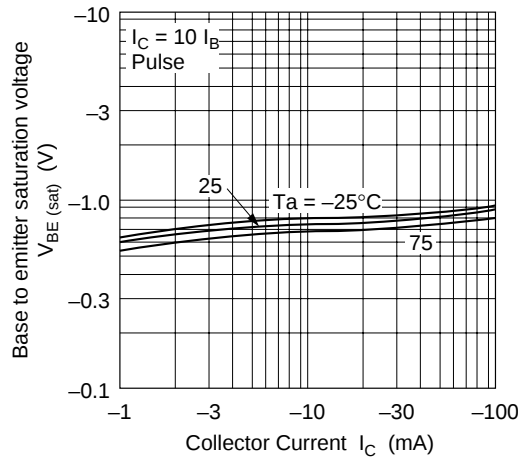
DC Current Transfer Ratio vs.
Collector Current



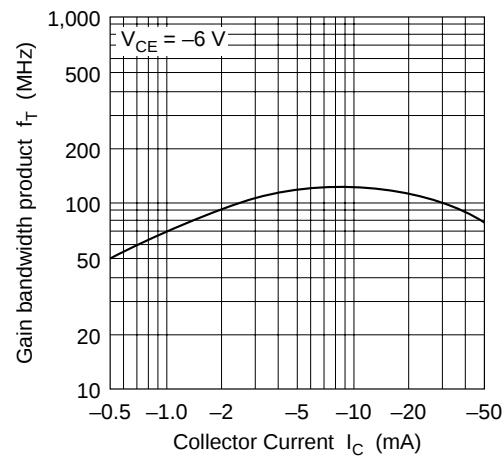
Collector to Emitter Saturation Voltage vs.
Collector Current

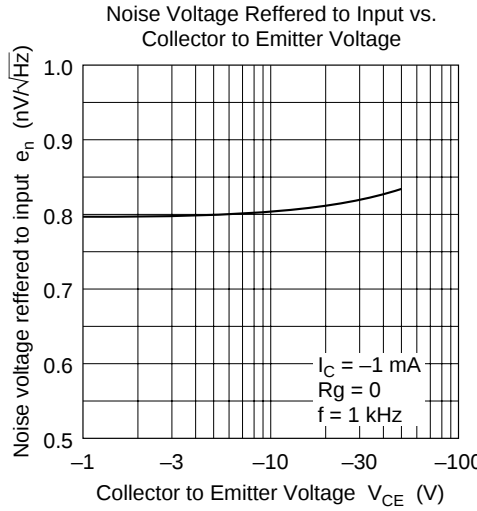
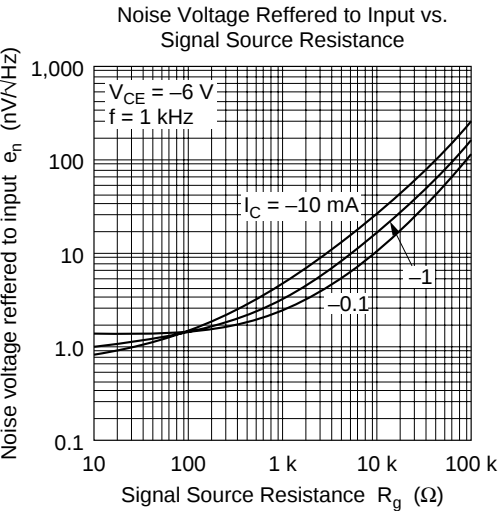
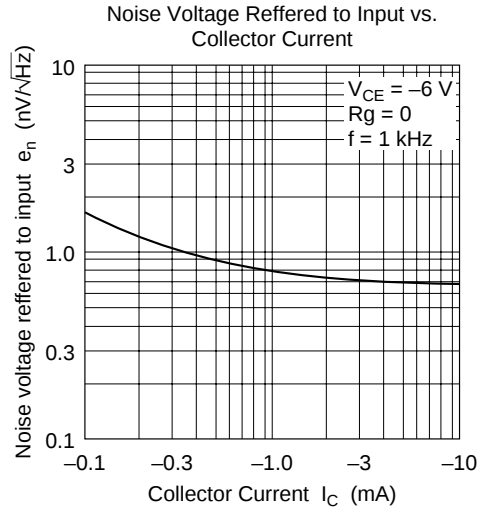
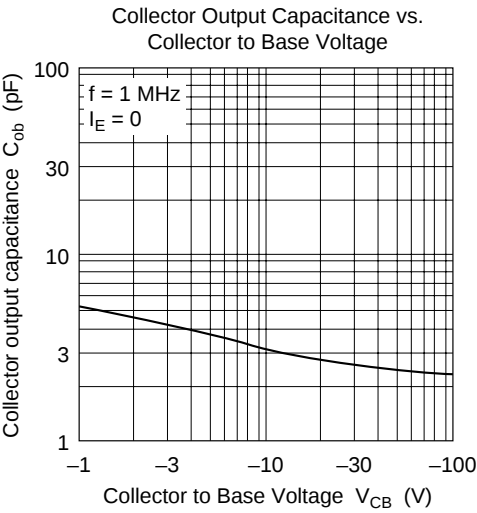


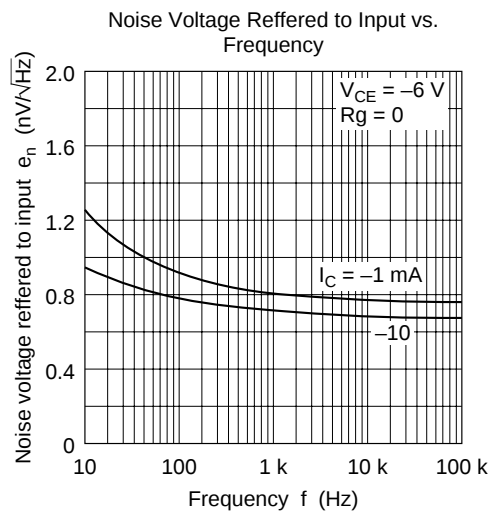
Base to Emitter Saturation Voltage vs.
Collector Current

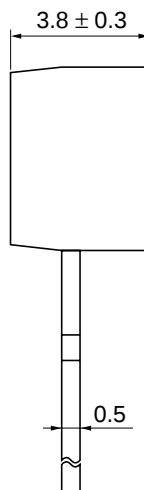
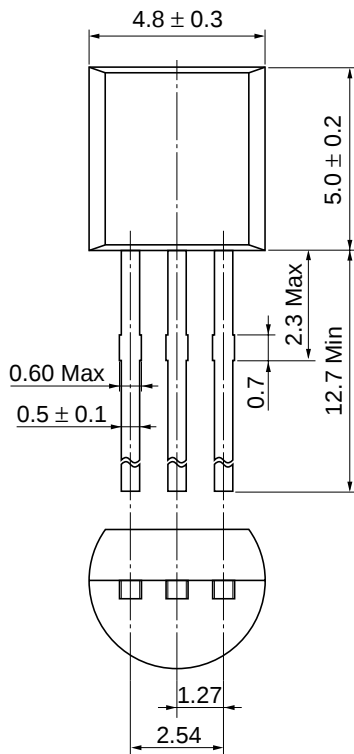


Gain Bandwidth Product vs.
Collector Current









Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

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Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose, CA 95134 Tel: <1> (408) 433-1990 Fax: <1> (408) 433-0223	Hitachi Europe GmbH Electronic components Group Dornacher Straße 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 778322
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Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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